

Description

The SX3P06AI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.

General Features

$V_{DS} = -60V$ $I_D = -3A$

$R_{DS(ON)} < -180m\Omega$ @ $V_{GS} = -10V$

Application

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3.3	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-1.4	A
I_{DM}	Pulsed Drain Current ²	-7	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	80	$^\circ C/W$

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=-250\mu\text{A}$	-60	---	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.021	---	$\text{V}/^\circ\text{C}$
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=-10\text{V}$, $I_D=-1.5\text{A}$	---	130	185	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$, $I_D=-1\text{A}$	---	158	200	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=-250\mu\text{A}$	-1.0	---	-2.5	V
$\Delta V_{\text{GS(th)}}$	$V_{\text{GS(th)}}$ Temperature Coefficient		---	4.08	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=-48\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{\text{DS}}=-48\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{\text{DS}}=-5\text{V}$, $I_D=-1.5\text{A}$	---	5.9	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{\text{DS}}=-20\text{V}$, $V_{\text{GS}}=-4.5\text{V}$, $I_D=-1.5\text{A}$	---	4.6	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	1.62	---	
$T_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DS}}=-15\text{V}$, $V_{\text{GS}}=-10\text{V}$, $R_G=3.3\Omega$, $I_D=-1\text{A}$	---	17.4	---	ns
T_r	Rise Time		---	5.4	---	
$T_{\text{d(off)}}$	Turn-Off Delay Time		---	37.2	---	
T_f	Fall Time		---	2.4	---	
C_{iss}	Input Capacitance	$V_{\text{DS}}=-15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	531	---	pF
C_{oss}	Output Capacitance		---	59	---	
C_{rss}	Reverse Transfer Capacitance		---	38	---	
I_s	Continuous Source Current ^{1,4}	$V_G=V_D=0\text{V}$, Force Current	---	---	-1.7	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-7	A
V_{SD}	Diode Forward Voltage ²	$V_{\text{GS}}=0\text{V}$, $I_s=-1\text{A}$, $T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$ 3.The power dissipation is limited by 150°C junction temperature4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

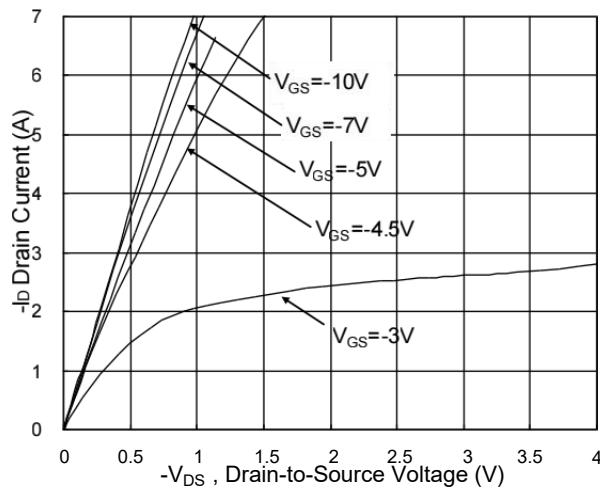


Fig.1 Typical Output Characteristics

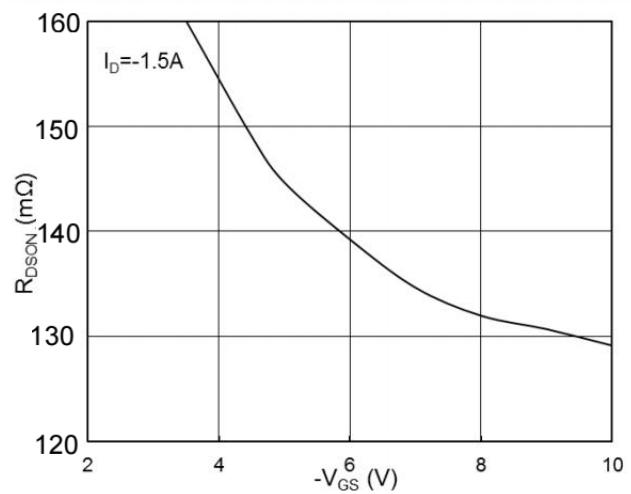


Fig.2 On-Resistance v.s Gate-Source

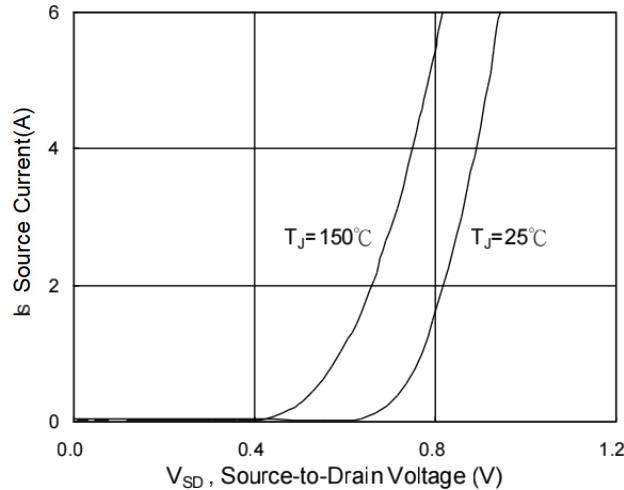


Fig.3 Forward Characteristics Of Reverse

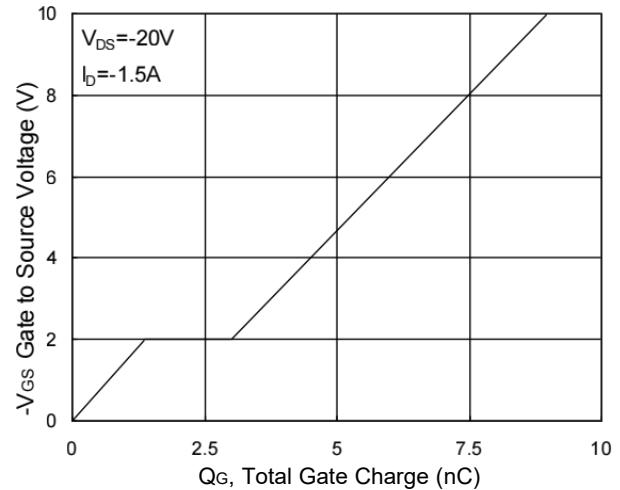


Fig.4 Gate-Charge Characteristics

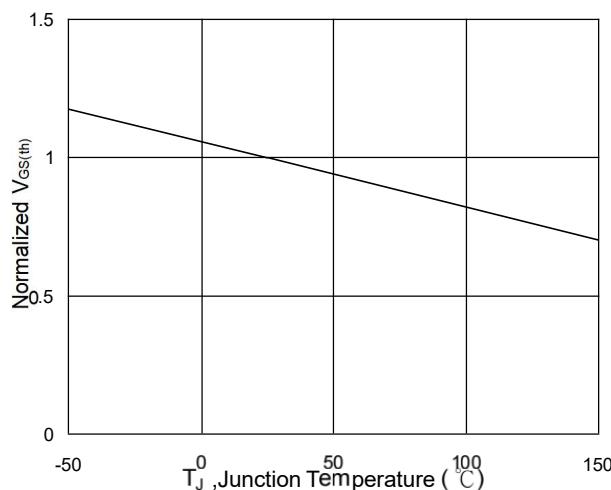


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

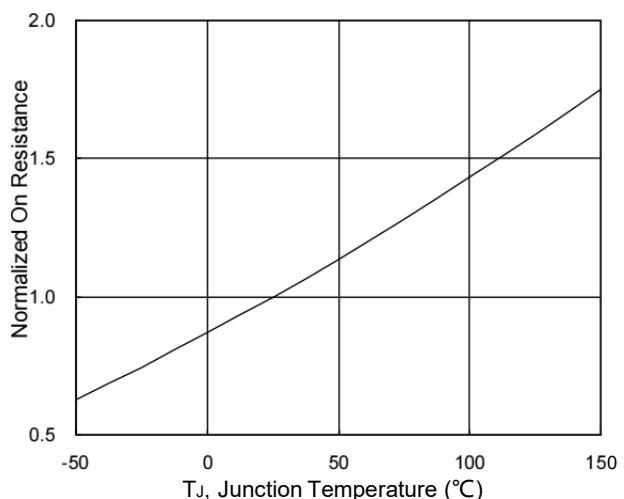


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

Typical Characteristics

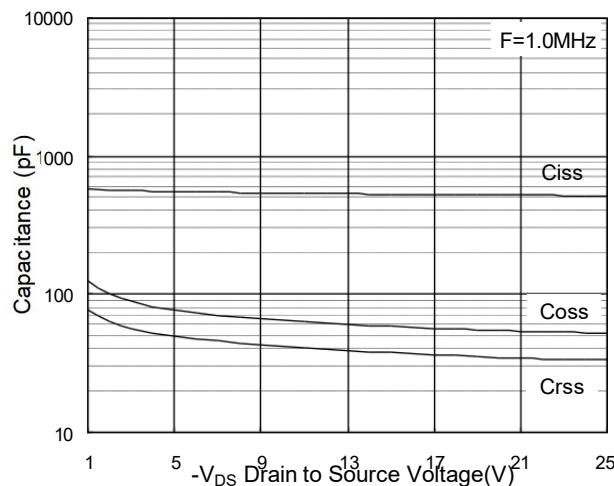


Fig.7 Capacitance

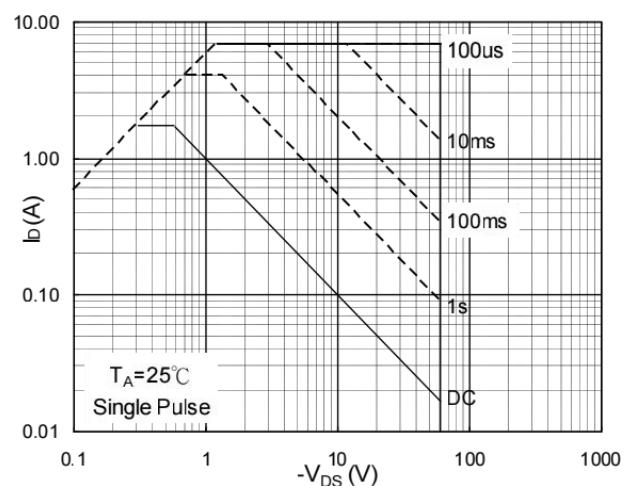


Fig.8 Safe Operating Area

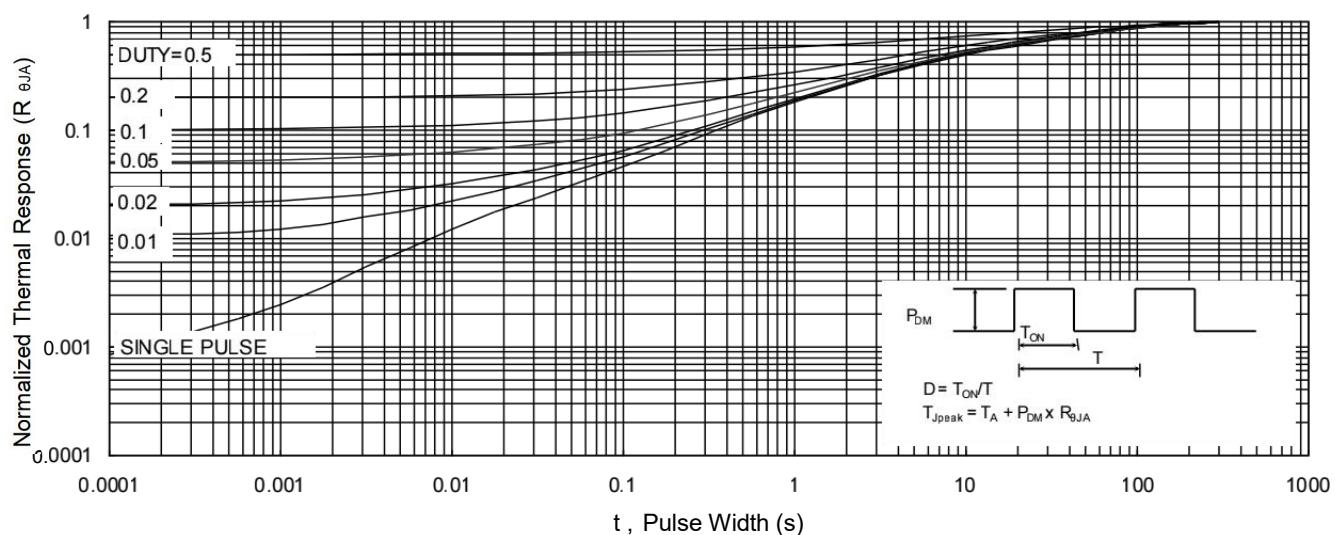


Fig.9 Normalized Maximum Transient Thermal Impedance

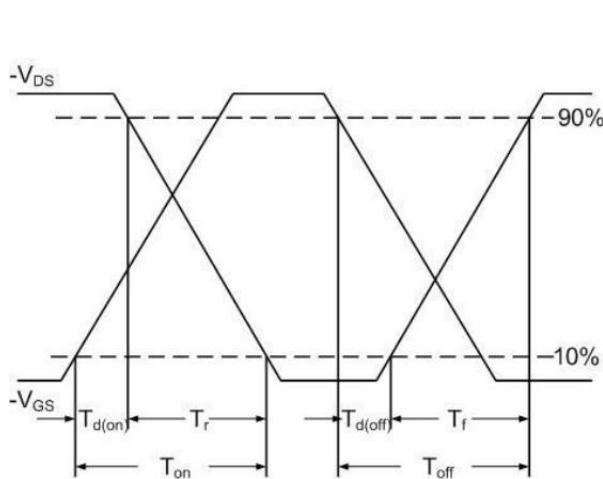


Fig.10 Switching time waveform

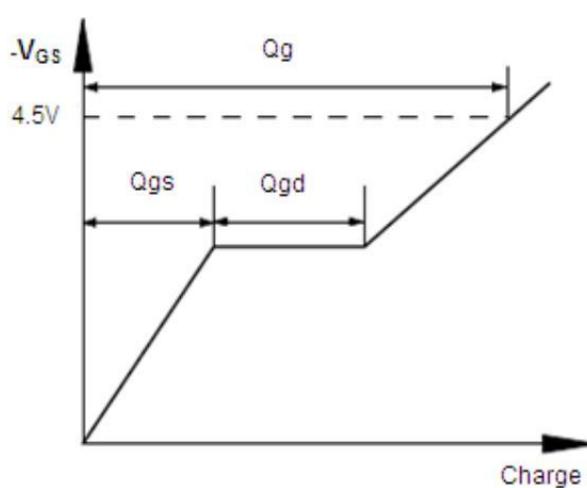
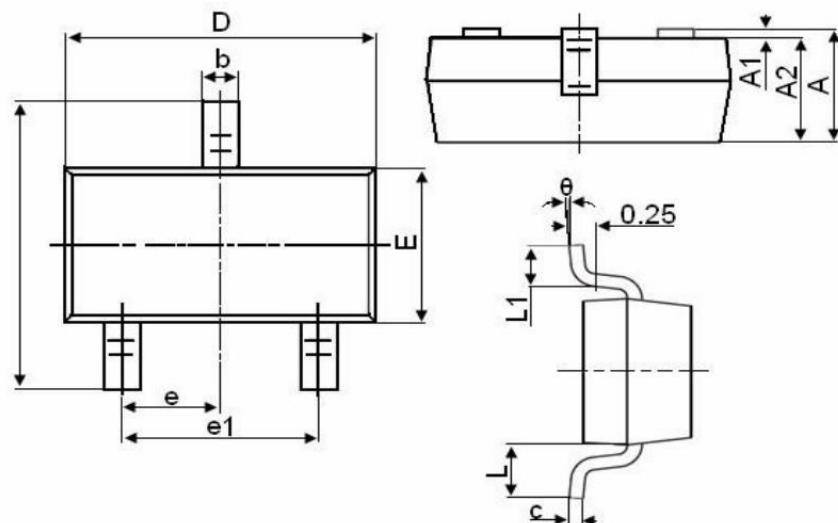


Fig.11 Gate Charge waveform

Package Mechanical Data-SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23		3000